Abstracts

High performance single supply power amplifiers for GSM and DCS applications using true enhancement mode FET technology (2002 Vol. I [MWSYM])

E. Glass, M. Shields and A. Reyes. "High performance single supply power amplifiers for GSM and DCS applications using true enhancement mode FET technology (2002 Vol. I [MWSYM])." 2002 MTT-S International Microwave Symposium Digest 02.1 (2002 Vol. I [MWSYM]): 557-560 vol.1.

Two high performance single supply power amplifier IC products have been developed for GSM and DCS applications using true enhancement mode FET technology. At VD=3.2V, under CW conditions, the GSM IC supplies +35.5 dBm output power at 58% PAE and the DCS IC supplies +33.5 dBm at 46% PAE. These ICs have low leakage currents similar to HBT and LDMOS and do not require the use of a drain switch. In addition, due to a high threshold voltage (Vth =+0.6V), they exhibit excellent RF isolation at Vref=0.1V and Pin=+5 dBm and do not require on-chip attenuators.

❑ Return to main document.